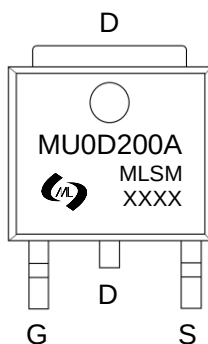


Features

- Trench Power LV MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$

Application

- High current load applications
- Load switching
- Hard switched and high frequency circuits

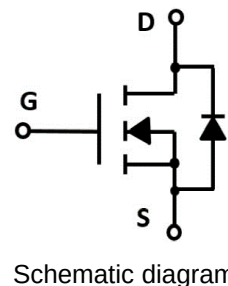


Marking and pin assignment

MU0D200A: Device code
XXXX : Code

Product Summary

V_{DS}	$R_{DS(ON)}$ TYP	I_D
30V	1.6m Ω @10V	200A
	2.6m Ω @4.5V	



Halogen-Free

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Rating	Unit
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Common Ratings (TC=25°C Unless Otherwise Noted)

V _{DS}	Drain-Source Breakdown Voltage		30	V
V _{GS}	Gate-Source Voltage		±20	V
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-50 to 155	°C
I _S	Diode Continuous Forward Current	Tc=25°C	200	A

Mounted on Large Heat Sink

I_{DM}	Pulse Drain Current Tested	$T_C=25^\circ\text{C}$	700	A
I_D	Continuous Drain Current	$T_C=25^\circ\text{C}$	200	A
P_D	Maximum Power Dissipation	$T_C=25^\circ\text{C}$	69	W
E_{AS}	Single pulse avalanche energy ^{Note1}		46.5	mJ

Ordering Information (Example)

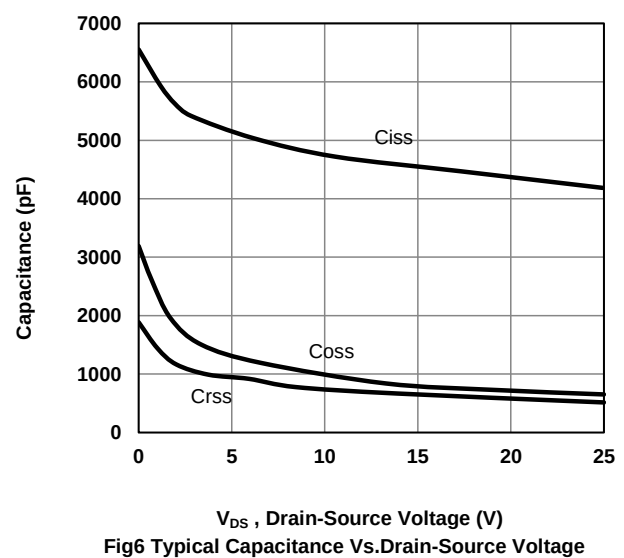
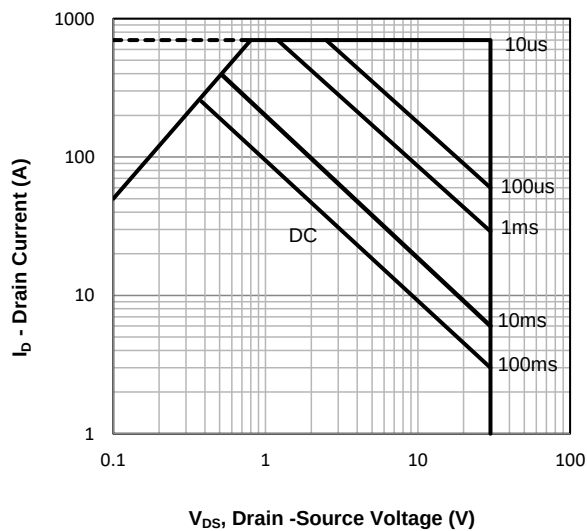
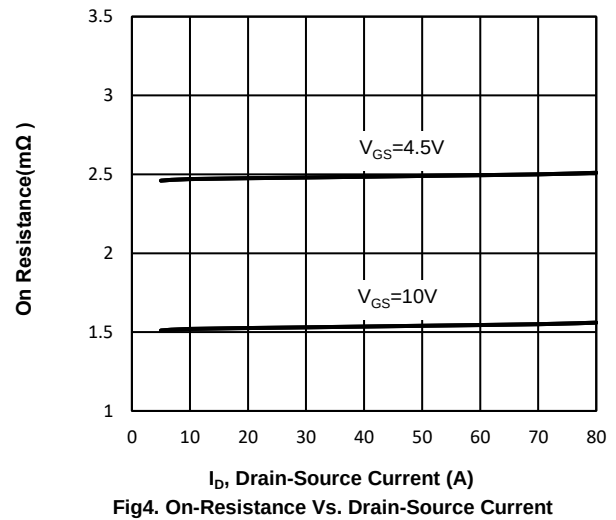
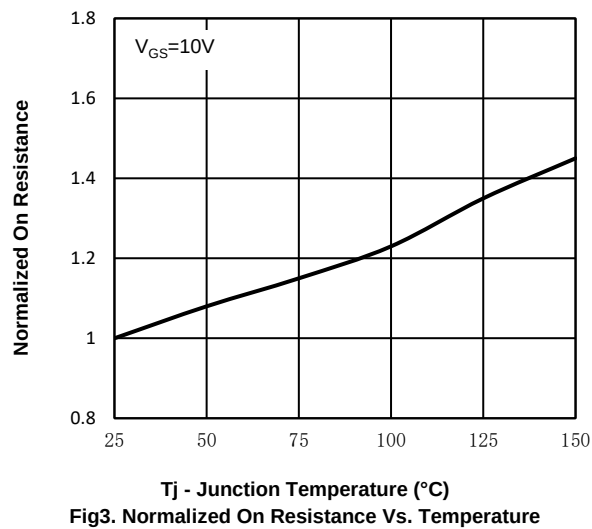
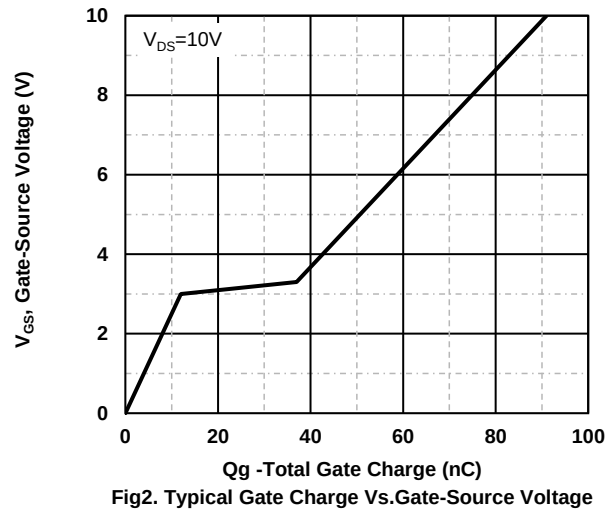
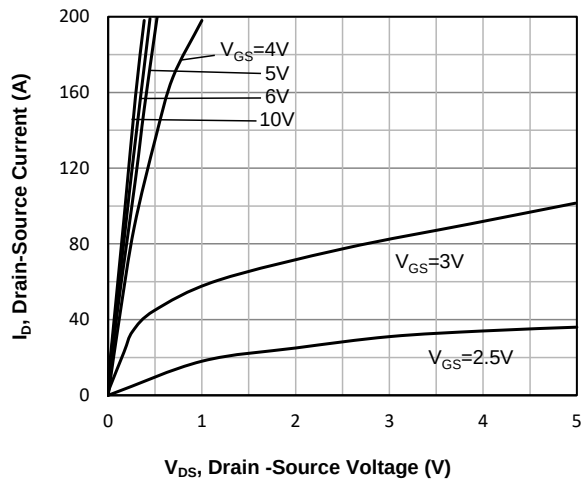
Type	Package	Marking	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
MU0D200A	TO-252	MU0D200A	2,500	5,000	35,000	13"reel

Electrical Characteristics (T _J =25℃ unless otherwise noted)						
Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ T _J = 25℃ (unless otherwise stated)						
B _{V(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	30	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} =0V	--	--	1.0	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V	--	--	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.0	1.5	2.5	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =10V, I _D =20A	--	1.6	2.0	mΩ
		V _{GS} =4.5V, I _D =20A	--	2.6	3.3	mΩ
Dynamic Electrical Characteristics @ T _J = 25℃ (unless otherwise stated)						
C _{ISS}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1MHz	--	4498	--	pF
C _{OSS}	Output Capacitance		--	800	--	pF
C _{RSS}	Reverse Transfer Capacitance		--	643	--	pF
Switching Characteristics						
Q _g	Total Gate Charge	V _{DS} =15V, I _D =20A, V _{GS} =10V	--	92.7	--	nC
Q _{gs}	Gate Source Charge		--	13.5	--	nC
Q _{gd}	Gate Drain Charge		--	22.8	--	nC
t _{d(on)}	Turn-on Delay Time	V _{DD} =20V, R _L =0.75Ω, V _{GS} =10V, R _G =3Ω	--	11	--	nS
t _r	Turn-on Rise Time		--	80	--	nS
t _{d(off)}	Turn-Off Delay Time		--	39	--	nS
t _f	Turn-Off Fall Time		--	92	--	nS
Source- Drain Diode Characteristics						
V _{SD}	Forward on voltage	T _J =25℃, I _S =20A	--	--	1.2	V

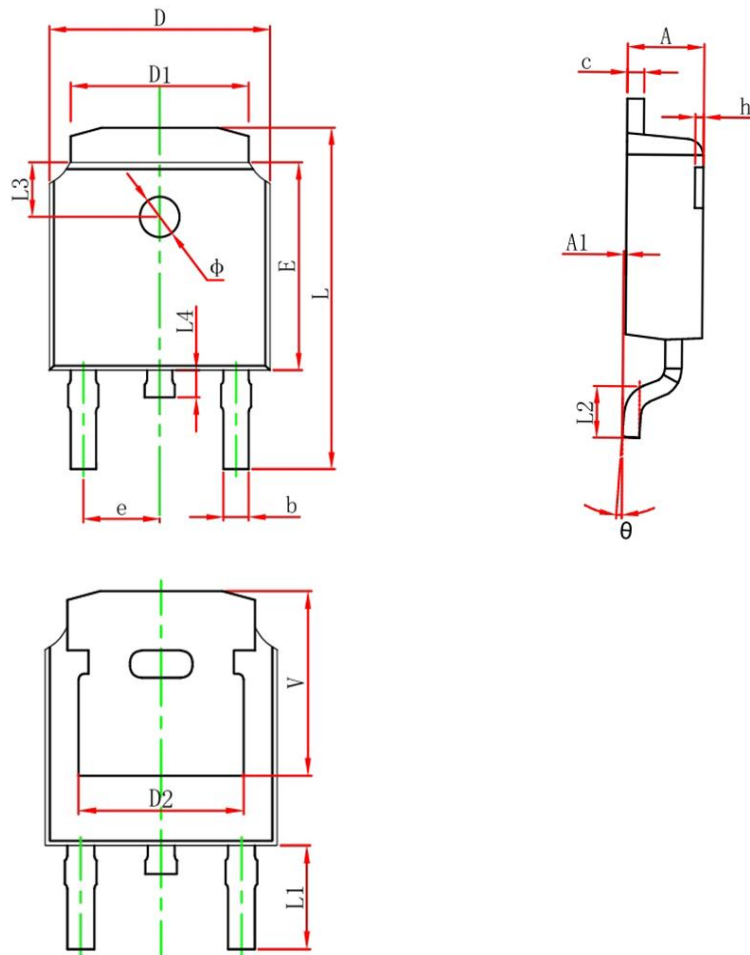
Note :

1、EAS Test Condition: L=2.0mH, I_{AS}=20A, V_{DD}=30V, V_{GS}=10V, I_{AS}=20A, T_J=25°C

Typical Operating Characteristics



TO-252 Package information



Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.635	0.770	0.025	0.030
c	0.450	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.712	10.312	0.386	0.406
L1	2.900 REF.		0.114 REF.	
L2	1.400	1.700	0.055	0.067
L3	1.600 REF.		0.063 REF.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.250 REF.		0.207 REF.	